Electronic Supplementary Information (ESI)

DPP-based small molecule, non-fullerene acceptors for "channel II" charge generation in OPVs and their improved performance in ternary cells

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1. ¹H and ¹³C NMR spectra



Figure S1. ¹H NMR spectra of *p*-DPP-PhCN.



Figure S2. ¹³C NMR spectra of *p*-DPP-PhCN.



Figure S3. ¹H NMR spectra of *m*-DPP-PhCN.



Figure S4. ¹³C NMR spectra of *m*-DPP-PhCN.



Figure S5. ¹H NMR spectra of *o*-DPP-PhCN.



Figure S6. ¹³C NMR spectra of *o*-DPP-PhCN.

2. Normalized UV absorption spectra



Figure S7. Normalized UV absorption spectra of DPP-PhCN acceptors in solution (solid lines) and film (symbols).

3. OPV characteristics

Active layer	D/A ratio	Annealing Temp (°C)	V _{OC} (V)	$J_{\rm SC}$ (mA/cm ²)	FF (%)	PCE (%)
РЗНТ: <i>р</i>-DPP-PhCN	1:2	90	0.59	1.52	40	0.35
		120	0.38	1.44	40	0.22
		150	0.15	0.78	37	0.04
	1:1	90	0.78	1.24	37	0.36
		120	0.56	1.64	50	0.47
		150	0.28	0.73	43	0.09
	2:1	90	0.47	1.01	49	0.23
		120	0.44	1.48	54	0.35
		150	0.24	1.18	46	0.13
РЗНТ: <i>т-DPP-PhCN</i>	1:2	90	0.51	0.43	29	0.06
		120	0.55	0.58	32	0.10
		150	0.32	0.30	29	0.03
	1:1	90	0.43	0.47	30	0.06
		120	0.45	0.56	31	0.08
		150	0.28	0.29	36	0.03
	2:1	90	0.45	0.36	33	0.05
		120	0.51	0.33	27	0.05
		150	0.26	0.18	35	0.02
P3HT: <i>o</i>-DPP-PhCN	1:2	90	1.09	1.14	34	0.43
		120	1.07	1.22	28	0.37
		150	0.12	0.42	32	0.02
	1:1	90	1.08	0.81	46	0.40
		120	1.09	1.19	35	0.46
		150	0.25	0.39	36	0.04
	2:1	90	1.09	0.92	44	0.44
		120	1.09	1.17	36	0.46
		150	0.58	0.82	45	0.22

Table S1. Photovoltaic performances with various blend ratios and annealing temperatures ^{*a*}

^a Devices are spin-coated from a chloroform solution and annealed for 10 min



Figure S8. J-V curves of OPV devices using chloroform as a solvent with various blend ratios and annealing temperatures.

4. Atomic force microscopy (AFM) images



Figure S9. AFM images $(10 \times 10 \ \mu\text{m})$ of the (a) Device I (P3HT:*p*-**DPP-PhCN** = 1:1, rms = 4.97 nm), (b) Device II (P3HT:*o*-**DPP-PhCN**:*p*-**DPP-PhCN** = 1:0.25:0.75, rms = 11.49 nm), (c) Device III (P3HT:*o*-**DPP-PhCN**:*p*-**DPP-PhCN** = 1:0.5:0.5, rms = 8.20 nm), (d) Device IV (P3HT:*o*-**DPP-PhCN**:*p*-**DPP-PhCN** = 1:0.75:0.25, rms = 2.95 nm), (e) Device V (P3HT:*o*-**DPP-PhCN** = 1:1, rms = 4.71 nm), and (f) P3HT:*o*-**DPP-PhCN**:*p*-**DPP-PhCN** = 1:0.25:0.75 (rms = 6.26 nm). The films were annealed at 120 °C (a–e) or 90 °C (f).